

Features

- High Speed CMOS Technology
- Single Channel
- Positive Voltage Control
- Low Power Dissipation
- Low Cost Plastic SOIC-8 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free “Green” Mold Compound
- 260°C Reflow Compatible
- MADRCC0006 is RoHS* Compliant Version of SWD-109

Description

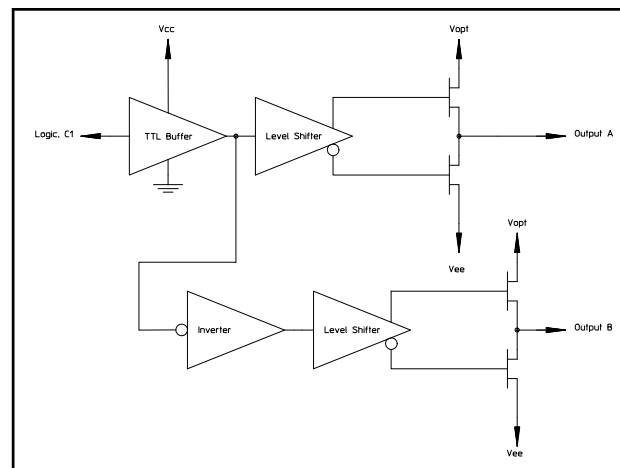
The MADRCC0006 is a single channel driver used to translate TTL control inputs into gate control voltages for GaAs FET microwave switches and attenuators. High speed analog CMOS technology is utilized to achieve low power dissipation at moderate to high speeds, encompassing most microwave switching applications. The output HIGH level is optionally 0 to +2.0V (relative to GND) to optimize the intermodulation products of the control devices at low frequencies.

Ordering Information¹

Part Number	Package
MADRCC0006	SOIC-8
MADRCC0006TR	1000 piece reel of SOIC-8
MADR-009151-000DIE	Die ²

1. Reference Application Note M513 for reel size information.
2. Die sales are available in waffle packs in increments of 100 pieces.

Functional Schematic



Pin Configuration³

Pin No.	Function
1	Output A
2	GND
3	Vcc
4	C1, Logic
5	Vee
6	Vopt
7	GND
8	Output B

3. The bottom of the die should be isolated for part number MADR-009151-000DIE.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

Guaranteed Operating Ranges

Symbol	Parameter ⁴	Unit	Min.	Typ.	Max.
V _{CC}	Positive DC Supply Voltage	V	4.5	5.0	5.5
V _{EE}	Negative DC Supply Voltage	V	-8.5	-5.0	-4.5
V _{OPT} ⁵	Optional DC Output Supply Voltage	V	0	1.0	2.0
V _{OPT} -V _{EE}	Negative Supply Voltage Range	V	4.5	6.5	11.0
V _{CC} -V _{EE}	Positive to negative Supply Range	V	9.0	10.0	14.0
T _A	Operating Ambient temperature	°C	-40	+25	+85
I _{OH}	DC Output Current - High	mA	—	—	-1.0
I _{OL}	DC Output Current - Low	mA	—	—	1.0
T _{rise} , T _{fall}	Maximum Input Rise or Fall Time	ns	—	—	500

4. All voltages are relative to GND.

5. V_{OPT} is grounded for most applications. To improve the intermodulation performance and the 1 dB compression point of GaAs control devices at low frequencies, V_{OPT} can be increased to between 1.0 and 2.0V. The nonlinear characteristics of the GaAs control devices will approximate performance at 500 MHz. It should be noted that the control current is on the GaAs MMICs will increase when positive controls are applied.

DC Characteristics over Guaranteed Operating Range

Symbol	Parameter	Test Conditions		Units	Min.	Typ.	Max.
V _{IH}	Input High Voltage	Guaranteed High Input Voltage		V	2.0	—	—
V _{IL}	Input Low Voltage	Guaranteed Low Input Voltage		V	—	—	0.8
V _{OH}	Output High Voltage	I _{OH} = -1 mA	V _{EE} = Max	V	V _{OPT} - 0.1	—	—
V _{OL}	Output Low Voltage	I _{OL} = 1 mA	V _{EE} = Max	V	—	—	V _{EE} + 0.1
I _{IN}	Input Leakage Current	V _{IN} = V _{CC} or GND	V _{EE} = Min	μA	—	.01	10
I _{CC}	Quiescent Supply Current	V _{CC} = Max V _{OPT} = Min or Max	V _{EE} = Min V _{IN} = V _{CC} or GND	μA	—	—	100
Δ I _{CC}	Additional Supply Current, per TTL Input pin	V _{CC} = Max	V _{IN} = V _{CC} - 2.1V	mA	—	—	1.0

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Silicon Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Truth Table

Input	Outputs	
C1	A	B
Logic "0"	V _{EE}	V _{OPT}
Logic "1"	V _{OPT}	V _{EE}

AC Characteristics Over Guaranteed Operating Range⁶

Symbol	Parameter	-55 to +25°C	≤+85°C	≤+125°C	Unit
T _{PLH}	Propagation Delay	22	25	30	ns
T _{PHL}	Propagation Delay	22	25	30	ns
T _{TLH}	Output Rising Transition Time	9.0	9.0	9.0	ns
T _{THL}	Output Falling Transition Time	8.0	8.0	8.0	ns
T _{skew}	Delay Skew, Output A to Output B	4.0	4.0	4.0	ns
C _{IN}	Input Capacitance	10	10	10	pF
C _{PDC}	Power Dissipation Capacitance ⁷	10	10	10	pF
C _{PDE}	Power Dissipation Capacitance ⁷	140	140	140	pF

6. V_{CC} = 4.5V, V_{OPT} - V_{EE} = min or max, V_{OPT} = 0V, C_L = 25 pF, Trise, Tfall = 6ns. These conditions represent the worst case for slow delays.

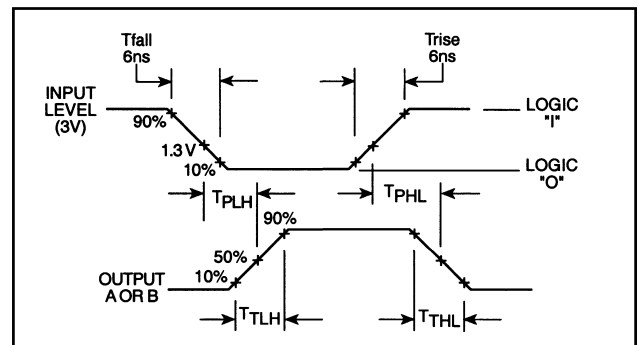
7. Total Power Dissipation is calculated by the following formula: PD = V_{CC}²fC_{PDC} + (V_{OPT}-V_{EE})²fC_{PDE}

Absolute Maximum Ratings^{8,9,10}

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	-0.5	7.0	V
V _{EE}	Negative DC Supply Voltage	-9.0	0.5	V
V _{OPT}	Optional DC Output Supply Voltage	-0.5	V _{CC} +0.5	V
V _{OPT} -V _{EE}	Output to Negative Supply Voltage Range	-0.5	11.0	V
V _{CC} -V _{EE}	Positive to Negative Supply Voltage Range	-0.5	14.0	V
V _I	DC Input Voltage	-0.5	V _{CC} +0.5	V
I _I	DC Input Current	-25	25	mA
V _O	DC Output Voltage	V _{EE} - 0.5	V _{OPT} +0.5	V
P _D ¹¹	Power Dissipation in Still Air	—	500	mW
V _O	DC Output Current	-25	25	mA
T _{STG}	Storage Temperature	-65	150	°C

8. All voltages are referenced to GND. All inputs and outputs incorporate latch-up protection structures.
9. Exceeding any one or combination of these limits may cause permanent damage to this device.
10. M/A-COM does not recommend sustained operation near these survivability limits.
11. Derate -7 mW/°C from 65°C to 85°C.

Switching Waveforms



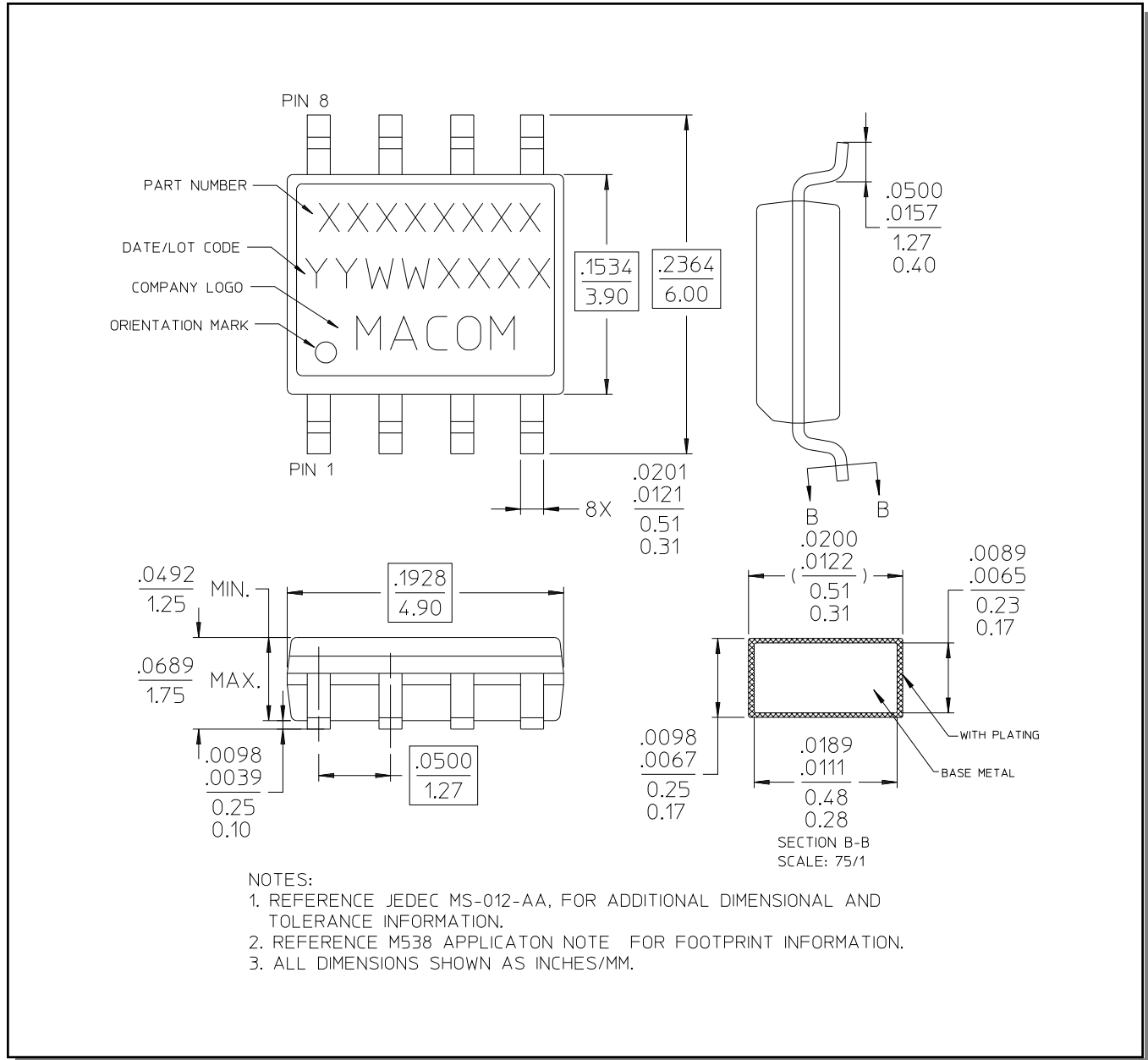
MADRCC0006, MADR-009151-000DIE



Single Driver for GaAs FET Switches and Attenuators

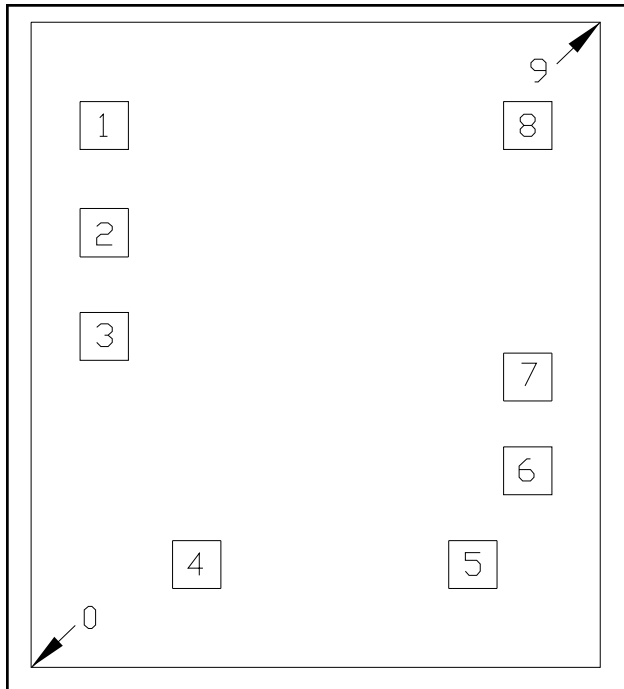
Rev. V5

Lead-Free, SOIC-8[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.

Outline Drawing



Pad Configuration^{12,13}

Die Size: 1080 x 1240 μm (nominal)

Pad No.	X (μm) nominal	Y (μm) nominal	Pad Size (μm)
0	0	0	Lower left edge of die
1	138	1042	92 x 92
2	138	835.5	92 x 92
3	138	636.75	92 x 92
4	313.75	198	92 x 92
5	838.5	198	92 x 92
6	942	378	92 x 92
7	942	558	92 x 92
8	942	1042	92 x 92
9	1080	1240	Upper right edge of die

12. All X,Y dimensions are at bond pad center.
 13. Die thickness is 9.5 mils.